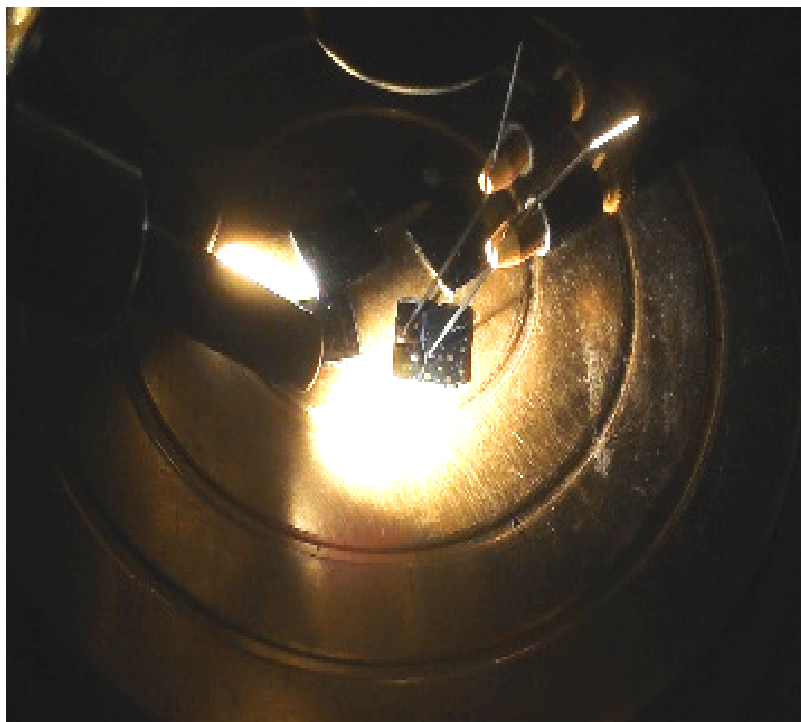


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From Jun 4, 2016 till Jun 11, 2016 we were visiting Helmholtz-Zentrum Dresden-Rossendorf in Dresden (HZDR). Under the supervision of Dr. Sehngqiang Zhou, we have perfected our skills of conducting room temperature electroluminescence (EL) measurements of ZnO/GaN heterojunctions grown by Molecular Beam Epitaxy (MBE) technique. A special series of heterojunction samples was prepared for this purpose in the Institute of Physics PAS (IP PAS). The goal of our visit was fulfilled, which means that we got to know the measurement system, we had the opportunity to see and compare different EL measurement methods and finally were able to conduct experiments without direct supervision. Together with German scientists, we discussed and interpreted results of EL. Additionally, sharing information about interests, measuring possibilities, growth techniques used in both institutions, led to a discussion about future possible cooperation, which was concluded with a joint proposal for a grant application.



One of the core-research areas of Dresden Institute of Ion Beam Physics and Materials Research HZDR group is the physics of ZnO structures for optoelectronic applications. Due to similar research profiles of our groups, we had an opportunity to deepen our knowledge about ZnO and defects in semiconductors. Discussions and data exchange with the scientists in the topic of optical properties of ZnO will lead to a wider understanding of processes influencing them and help in the interpretation of the results of our research in IP PAS.